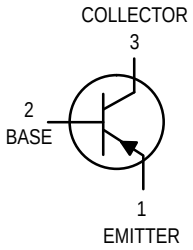
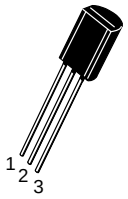
One Watt Amplifier Transistors

PNP Silicon

BDB02C,D





CASE 29–05, STYLE 1
TO–92 (TO–226AE)

MAXIMUM RATINGS

Rating	Symbol	BDB02C	BDB02D	Unit
Collector–Emitter Voltage	V_{CEO}	–80	–100	Vdc
Collector–Base Voltage	V_{CES}	–80	–100	Vdc
Emitter–Base Voltage	V_{EBO}	–5.0		Vdc
Collector Current — Continuous	I_C	–0.5		Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.0 8.0		Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	2.5 20		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Voltage (I_C = –10 mA, I_B = 0)	BDB02C BDB02D	$V_{(BR)CEO}$	–80 –100	— —	Vdc
Collector Cutoff Current (V_{CB} = –80 V, I_E = 0) (V_{CB} = –100 V, I_E = 0)	 BDB02C BDB02D	I_{CBO}	 — —	 –0.1 –0.1	μAdc
Emitter Cutoff Current (I_C = 0, V_{EB} = –5.0 V)		I_{EBO}	—	–100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = –100 mA, V_{CE} = –1.0 V) (I_C = –500 mA, V_{CE} = –2.0 V)		h_{FE}	 40 25	 400 —	—
Collector–Emitter Saturation Voltage(1) (I_C = –1000 mA, I_B = –100 mA)		$V_{CE(sat)}$	—	–0.7	Vdc
Collector–Emitter On Voltage(1) (I_C = –1000 mA, V_{CE} = –1.0 V)		$V_{BE(on)}$	—	–1.2	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (I_C = –200 mA, V_{CE} = –5.0 V, f = 20 MHz)		f_T	50	—	MHz
Output Capacitance (V_{CB} = –10 V, I_E = 0, f = 1.0 MHz)		C_{ob}	—	30	pF

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle 2.0%.

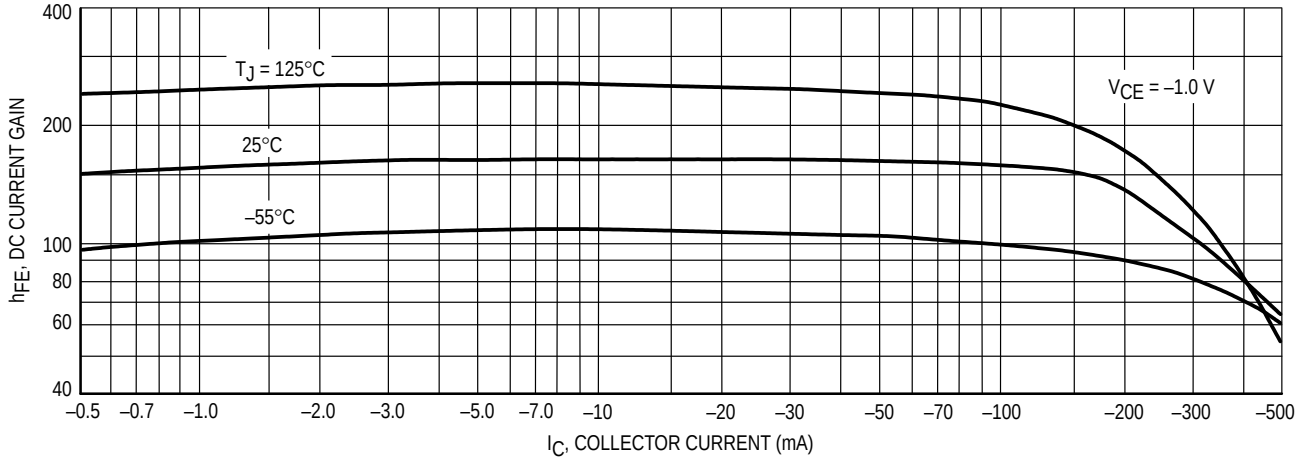


Figure 1. DC Current Gain

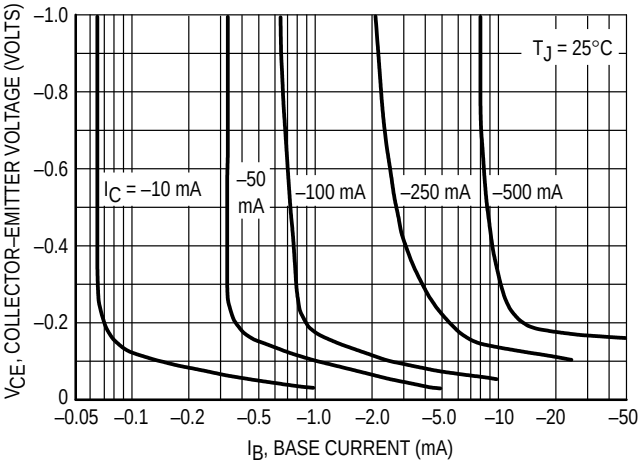


Figure 2. Collector Saturation Region

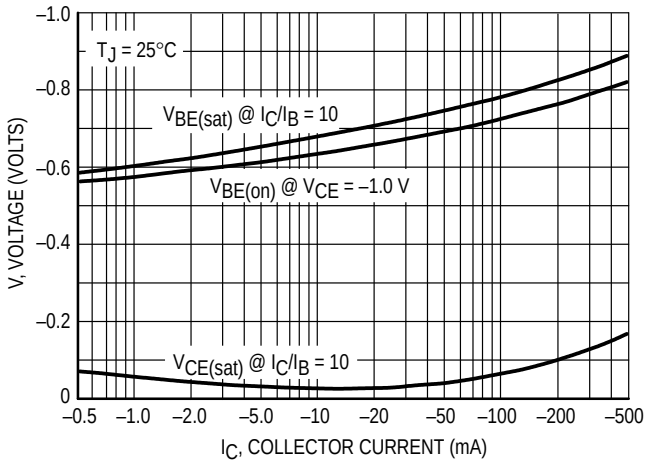


Figure 3. On Voltages

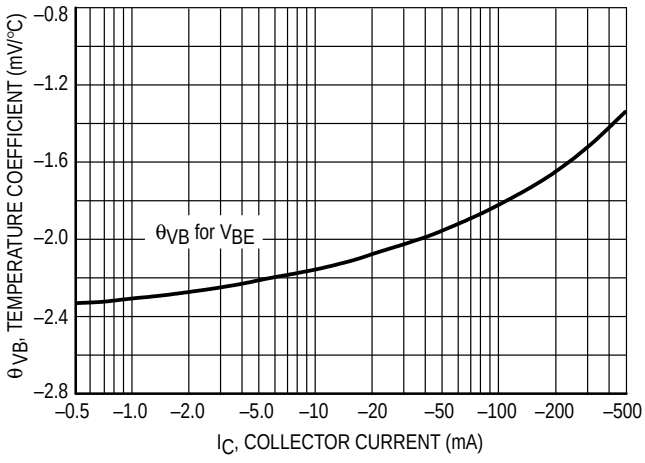


Figure 4. Base–Emitter Temperature Coefficient

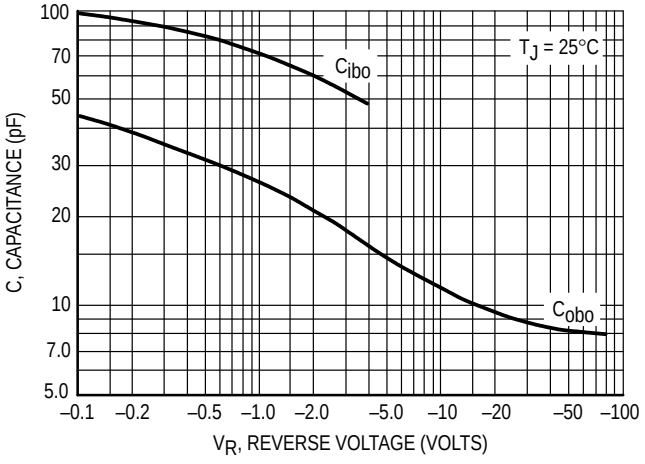


Figure 5. Capacitance

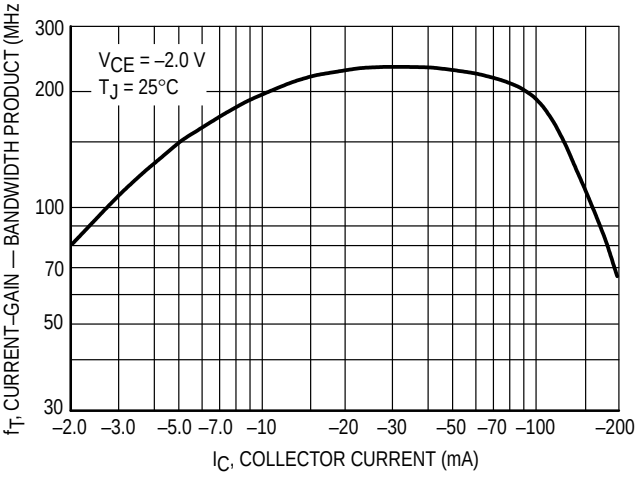


Figure 6. Current–Gain — Bandwidth Product

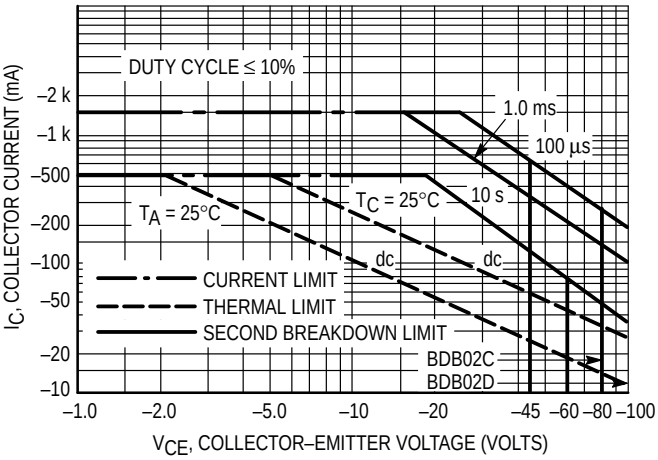
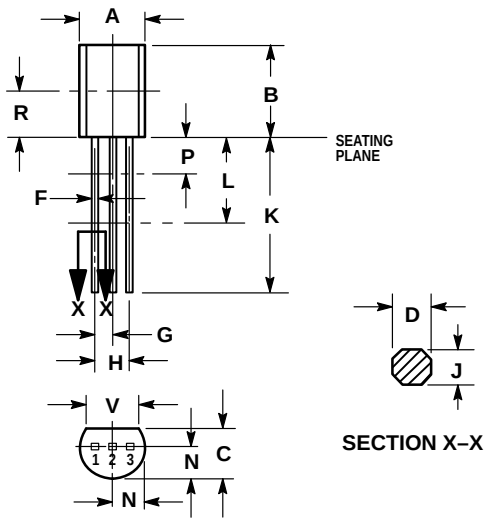


Figure 7. Active Region — Safe Operating Area

PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSIONS D AND J APPLY BETWEEN L AND K MIMIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.022	0.46	0.56
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.135	—	3.43	—
V	0.135	—	3.43	—

CASE 029–05
(TO–226AE)
ISSUE AD

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

How to reach us:
USA/EUROPE: Motorola Literature Distribution;
P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447

MFAX: RMFAX0@email.sps.mot.com – TOUCHTONE (602) 244–6609
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JAPAN: Nippon Motorola Ltd.; Tatsumi–SPD–JLDC, Toshikatsu Otsuki,
6F Seibu–Butsuryu–Center, 3–14–2 Tatsumi Koto–Ku, Tokyo 135, Japan. 03–3521–8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298